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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DkD	A263	5,089,872	02/18/1992	Ozturk et al.			
DkD	A264	5,242,847	09/07/1993	Ozturk et al.			
DkD	A265	5,548,128	08/20/1996	Soref et al.			
DkD	A266	5,607,876	03/04/1997	Biegelsen et al.			
DkD	A267	5,821,577	10/13/1998	Crabbé et al.			

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
DkD	C159	Hamada et al., "A New Aspect of Mechanical Stress Effects in Scaled MOS Devices," <u>IEEE Transactions on Electron Devices</u> , Vol. 38, No. 4 (April 1991), pp. 895-900.
DkD	C160	Huang et al., "Isolation Process Dependence of Channel Mobility in Thin-Film SOI Devices," <u>IEEE Electron Device Letters</u> , Vol. 17, No. 6 (June 1996), pp. 291-293.
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DkD	C162	Iida et al., "Thermal behavior of residual strain in silicon-on-insulator bonded wafer and effects on electron mobility," <u>Solid-State Electronics</u> , Vol. 43 (1999), pp. 1117-1120.
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DkD	C164	Klauk et al., "Thermal stability of undoped strained Si channel SiGe heterostructures," American Institute of Physics, April 1, 1996, pgs. 1975-1977.
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